

INFORMATION DISCLOSURE CITATION

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Applicants	Hiroki SAKURAI et al.		
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U.S. PATENT DOCUMENTS							
Examiner Initial*		Document Number	Issue Date	Name	Class	Sub Class	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS							
		Document Number	Publication Date	Country	Class	Sub Class	Translation Yes or No
<u>TN</u>		2003-234325	08/22/03	JAPAN			ABSTRACT
<u>TN</u>		2003-282734	10/03/03	JAPAN			ABSTRACT

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
<u>TN</u>	LEE, J. H. et al., "Mass Production Worthy HfO ₂ -Al ₂ O ₃ Laminate Capacitor Technology Using Hf Liquid Precursor for Sub-100nm DRAMs", IEEE, 4 pages, (2002).
	GUTSCHE, M. et al., "Capacitance Enhancement Techniques for Sub-100nm Trench DRAMs", IEEE, 4 pages, (2001).
<u>TN</u>	SEIDL, H. et al., "A Fully Integrated Al ₂ O ₃ Trench Capacitor DRAM for Sub-100nm Technology", IEEE, 4 pages, (2002).

Examiner	<u>[Signature]</u>	Date Considered	1/13/06
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